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TECHNOLOGY CENTER

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes  
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Docket No.: 303.229US2  
Filed: August 11, 1998  
Examiner: Mark Prenty

Serial No.: 09/132,157  
Due Date: March 15, 1999  
Group Art Unit: 2822

Assistant Commissioner for Patents  
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ An Amendment and Response (14 Pages).
- ☒ A Supplemental Information Disclosure Statement (1 pgs.), Form 1449 (1 pgs.), and copies of 1 cited references.
- ☒ A check in the amount of \$240.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).

**Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.**

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 15th day of March, 1999.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
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By: Thomas W. Leffert  
Atty: Thomas W. Leffert  
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(GENERAL)